

Silicon PNP Power Transistors

2SA1079

DESCRIPTION

- With TO-220 package
- High transition frequency
- Excellent safe operating area

APPLICATIONS

- High-frequency power amplifier
- Audio power amplifiers and drivers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

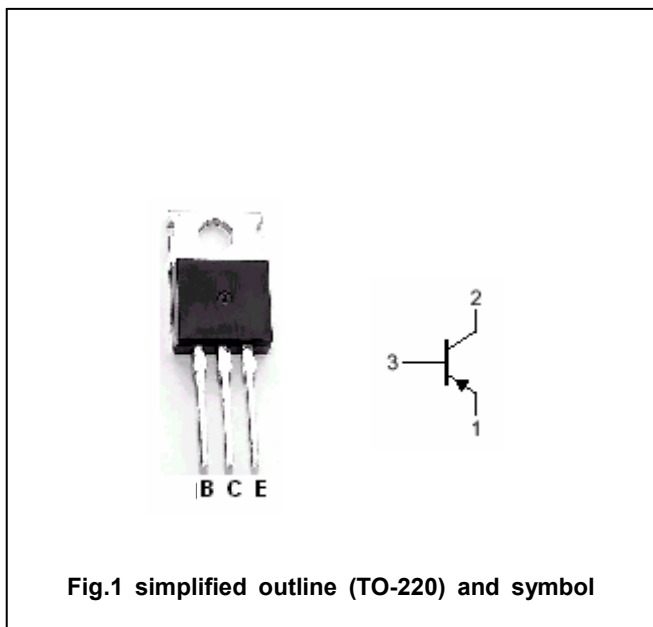


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-160	V
V _{CEO}	Collector-emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, R _{BE} =∞	-160			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1μA, I _E =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1μA, I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.7A; I _B =-70mA		-0.45	-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-0.7A; V _{CE} =-5V		-0.8	-1.7	V
I _{CBO}	Collector cut-off current	V _{CB} =-160V; I _E =0			-1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-160V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-0.3A; V _{CE} =-5V	100		350	
h _{FE-2}	DC current gain	I _C =-0.7A; V _{CE} =-5V	50			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V; f=10MHz		120		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-20V; f=1MHz		100		pF

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)